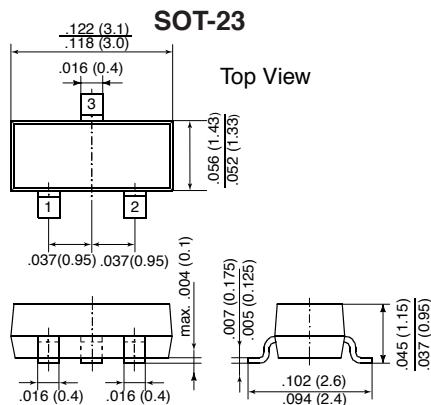
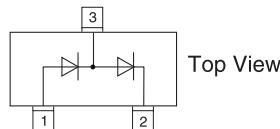


**MMBD7000****DUAL SMALL SIGNAL SWITCHING DIODE**

Dimensions in inches and (millimeters)

**FEATURES**

- ◆ Silicon Epitaxial Planar Diode
- ◆ Fast switching dual diode, especially suited for automatic insertion.

**MECHANICAL DATA****Case:** SOT-23 (TO-236AB) Plastic Package**Weight:** approx. 0.008 g**Marking Code:** M5C**MAXIMUM RATINGS AND THERMAL CHARACTERISTICS**

Ratings at 25°C ambient temperature unless otherwise specified (per diode)

	SYMBOL	VALUE	UNIT
Reverse Voltage	V <sub>R</sub>	100	Volts
Forward Current (continuous)	I <sub>F</sub>	200	mA
Non-Repetitive Peak Forward Current at t = 1s	I <sub>FSM</sub>	500	mA
Power Dissipation on FR-5 Board T <sub>A</sub> = 25°C Derate above 25°C	P <sub>tot</sub>	225 1.8	mW mW/°C
Total Device Dissipation on Alumina Substrate, T <sub>A</sub> = 25°C Derate above 25°C	P <sub>tot</sub>	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient Air	R <sub>θJA</sub>	417 <sup>(1)</sup> 556 <sup>(2)</sup>	°C/W
Maximum Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>s</sub>	-55 to +150	°C

**NOTES**

- (1) On Alumina Substrate  
(2) On FR-5 Board

# MMBD7000

## ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified (per diode).

	SYMBOL	MIN.	MAX.	UNIT
Reverse Breakdown Voltage at $I_R = 100\mu A$	$V_{BR}$	100	-	Volts
Leakage Current at $V_R = 50 V$ at $V_R = 100 V$ at $V_R = 50 V, T_j = 125^\circ C$	$I_R$ $I_R$ $I_R$	- - -	1.0 3.0 100	$\mu A$ $\mu A$ $\mu A$
Forward Voltage at $I_F = 1mA$ at $I_F = 10mA$ at $I_F = 100mA$	$V_F$ $V_F$ $V_F$	0.55 0.67 0.75	0.70 0.82 1.10	Volts Volts Volts
Capacitance at $V_R = 0; f = 1MHz$	$C_{tot}$	-	1.5	pF
Reverse Recovery Time from $I_F = 10mA$ to $I_R = 10 mA$ measured at $I_{rr} = 1mA, R_L = 100 \Omega$	$t_{rr}$	-	4.0	ns